

Bruno Daudin

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

351
papers

7,960
citations

49
h-index

74
g-index

362
ext. papers

8,329
ext. citations

2.8
avg, IF

5.46
L-index

#	Paper	IF	Citations
351	Europium-Implanted AlN Nanowires for Red Light-Emitting Diodes. <i>ACS Applied Nano Materials</i> , 2022 ,	5.6	1
350	Nanoscale imaging of dopant incorporation in n-type and p-type GaN nanowires by scanning spreading resistance microscopy. <i>Journal of Applied Physics</i> , 2022 , 131, 075701	2.5	
349	DX center formation in highly Si doped AlN nanowires revealed by trap assisted space-charge limited current. <i>Applied Physics Letters</i> , 2022 , 120, 162104	3.4	1
348	Growth of zinc-blende GaN on muscovite mica by molecular beam epitaxy. <i>Nanotechnology</i> , 2021 , 32, 025601	3.4	1
347	The role of surface diffusion in the growth mechanism of III-nitride nanowires and nanotubes. <i>Nanotechnology</i> , 2021 , 32, 085606	3.4	2
346	Eu ³⁺ optical activation engineering in Al Ga _{1-x} N nanowires for red solid-state nano-emitters. <i>Applied Materials Today</i> , 2021 , 22, 100893	6.6	1
345	Shallow donor and DX state in Si doped AlN nanowires grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 2021 , 119, 262105	3.4	2
344	Nanoscale x-ray investigation of composition fluctuations in AlGa _x N nanowires. <i>Nanotechnology</i> , 2020 , 31, 375709	3.4	2
343	Resonant Raman scattering of core-shell GaN/AlN nanowires. <i>Nanotechnology</i> , 2020 ,	3.4	1
342	Impact of kinetics on the growth of GaN on graphene by plasma-assisted molecular beam epitaxy. <i>Nanotechnology</i> , 2020 , 31, 115602	3.4	4
341	Role of Ga Surface Diffusion in the Elongation Mechanism and Optical Properties of Catalyst-Free GaN Nanowires Grown by Molecular Beam Epitaxy. <i>Nano Letters</i> , 2019 , 19, 4250-4256	11.5	8
340	Spontaneous intercalation of Ga and In bilayers during plasma-assisted molecular beam epitaxy growth of GaN on graphene on SiC. <i>Nanotechnology</i> , 2019 , 30, 375602	3.4	8
339	Vacancy-type defects in GaN self-assembled nanowires probed using monoenergetic positron beam. <i>Journal of Applied Physics</i> , 2019 , 125, 175705	2.5	1
338	Polarity conversion of GaN nanowires grown by plasma-assisted molecular beam epitaxy. <i>Applied Physics Letters</i> , 2019 , 114, 172101	3.4	8
337	Incorporation of Europium into GaN Nanowires by Ion Implantation. <i>Journal of Physical Chemistry C</i> , 2019 , 123, 11874-11887	3.8	7
336	Mg and In Codoped p-type AlN Nanowires for pn Junction Realization. <i>Nano Letters</i> , 2019 , 19, 8357-8364	11.5	19
335	Dopant radial inhomogeneity in Mg-doped GaN nanowires. <i>Nanotechnology</i> , 2018 , 29, 255706	3.4	17

334	Quantitative analysis of AlN/GaN HRTEM images 2018 , 301-304		
333	Axial p-n junction and space charge limited current in single GaN nanowire. <i>Nanotechnology</i> , 2018 , 29, 01LT01	3.4	6
332	Multiple optical centers in Eu-implanted AlN nanowires for solid-state lighting applications. <i>Applied Physics Letters</i> , 2018 , 113, 201905	3.4	6
331	Doping EGa ₂ O ₃ with europium: influence of the implantation and annealing temperature. <i>Journal Physics D: Applied Physics</i> , 2017 , 50, 325101	3	20
330	Growth and Structural Characterization of Self-Nucleated III-Nitride Nanowires. <i>Semiconductors and Semimetals</i> , 2017 , 96, 203-229	0.6	2
329	Direct assessment of p-n junctions in single GaN nanowires by Kelvin probe force microscopy. <i>Nanotechnology</i> , 2016 , 27, 385202	3.4	16
328	Picometre-precision atomic structure of inversion domain boundaries in GaN 2016 , 564-565		
327	Chemical composition fluctuations and strain relaxation in InGaN nanowires: The role of the metal/nitrogen flux ratio. <i>Materials Science in Semiconductor Processing</i> , 2016 , 55, 79-84	4.3	7
326	Lifetime Measurements Well below the Optical Diffraction Limit. <i>ACS Photonics</i> , 2016 , 3, 1157-1163	6.3	26
325	Quantum Dot-Like Behavior of Compositional Fluctuations in AlGaIn Nanowires. <i>Nano Letters</i> , 2016 , 16, 960-6	11.5	27
324	Unraveling the strain state of GaN down to single nanowires. <i>Journal of Applied Physics</i> , 2016 , 120, 225701	5	6
323	Direct Measurement of Polarization-Induced Fields in GaN/AlN by Nano-Beam Electron Diffraction. <i>Scientific Reports</i> , 2016 , 6, 28459	4.9	18
322	Optical properties of wurtzite GaN/AlN quantum dots grown on non-polar planes: The effect of stacking faults in the reduction of the internal electric field. <i>Materials Science in Semiconductor Processing</i> , 2016 , 49, 76-80	4.3	1
321	Correction to Spectroscopic Analysis of Eu ³⁺ Implanted and Annealed GaN Layers and Nanowires <i>Journal of Physical Chemistry C</i> , 2016 , 120, 6907-6908	3.8	5
320	InGaIn nanowires with high InN molar fraction: growth, structural and optical properties. <i>Nanotechnology</i> , 2016 , 27, 195704	3.4	14
319	Phonon-plasmon coupling in Si doped GaN nanowires. <i>Materials Science in Semiconductor Processing</i> , 2016 , 55, 63-66	4.3	2
318	Reprint of: Optical properties of wurtzite GaN/AlN quantum dots grown on non-polar planes: The effect of stacking faults in the reduction of the internal electric field. <i>Materials Science in Semiconductor Processing</i> , 2016 , 55, 90-94	4.3	
317	Growth mechanism of InGaIn nano-umbrellas. <i>Nanotechnology</i> , 2016 , 27, 455603	3.4	10

316	Spectroscopic Analysis of Eu ³⁺ Implanted and Annealed GaN Layers and Nanowires. <i>Journal of Physical Chemistry C</i> , 2015 , 119, 17954-17964	3.8	12
315	Si Donor Incorporation in GaN Nanowires. <i>Nano Letters</i> , 2015 , 15, 6794-801	11.5	61
314	Assessment of Polarity in GaN Self-Assembled Nanowires by Electrical Force Microscopy. <i>Nano Letters</i> , 2015 , 15, 6770-6	11.5	38
313	Attribution of the 3.45 eV GaN nanowires luminescence to inversion domain boundaries. <i>Applied Physics Letters</i> , 2015 , 107, 051904	3.4	42
312	The influence of AlN buffer over the polarity and the nucleation of self-organized GaN nanowires. <i>Journal of Applied Physics</i> , 2015 , 117, 245303	2.5	49
311	InGaN Nanowire Heterostructures 2014 , 41-60		
310	III-Nitride quantum dots in nanowires: growth, structural, and optical properties. <i>Turkish Journal of Physics</i> , 2014 , 38, 314-322	1.6	0
309	A polarity-driven nanometric luminescence asymmetry in AlN/GaN heterostructures. <i>Applied Physics Letters</i> , 2014 , 105, 143106	3.4	11
308	Cathodoluminescence of stacking fault bound excitons for local probing of the exciton diffusion length in single GaN nanowires. <i>Applied Physics Letters</i> , 2014 , 104, 102102	3.4	25
307	Anisotropic In distribution in InGaN core-shell nanowires. <i>Journal of Applied Physics</i> , 2014 , 116, 013517	2.5	7
306	GaN:Pr ³⁺ nanostructures for red solid state light emission. <i>RSC Advances</i> , 2014 , 4, 62869-62877	3.7	4
305	Ultraviolet Raman spectroscopy of GaN/AlN core-shell nanowires: Core, shell, and interface modes. <i>Applied Physics Letters</i> , 2013 , 102, 143109	3.4	14
304	Selective ion-induced intermixing and damage in low-dimensional GaN/AlN quantum structures. <i>Nanotechnology</i> , 2013 , 24, 505717	3.4	13
303	Strain assisted inter-diffusion in GaN/AlN quantum dots. <i>Journal of Applied Physics</i> , 2013 , 113, 034311	2.5	14
302	Splitting of surface-related phonons in Raman spectra of self-assembled GaN nanowires. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013 , 10, 519-522		3
301	Enhanced red emission from praseodymium-doped GaN nanowires by defect engineering. <i>Acta Materialia</i> , 2013 , 61, 3278-3284	8.4	22
300	A comparative study of photo-, cathodo- and ionoluminescence of GaN nanowires implanted with rare earth ions. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2013 , 306, 201-206	1.2	8
299	Growth, structural and optical properties of AlGaN nanowires in the whole composition range. <i>Nanotechnology</i> , 2013 , 24, 115704	3.4	56

298	Towards the understanding of the intentionally induced yellow luminescence in GaN nanowires. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013 , 10, 667-672		8
297	Probing alloy composition gradient and nanometer-scale carrier localization in single AlGaIn nanowires by nanocathodoluminescence. <i>Nanotechnology</i> , 2013 , 24, 305703	3.4	22
296	Splitting of the Surface Phonon Modes in Wurtzite Nanowires. <i>Japanese Journal of Applied Physics</i> , 2013 , 52, 08JL01	1.4	2
295	Size and shape effects in the Raman scattering by single GaN nanowires. <i>Journal of Applied Physics</i> , 2013 , 114, 223506	2.5	10
294	A geometrical model for the description of the AlN shell morphology in GaN-AlN core-shell nanowires. <i>Journal of Applied Physics</i> , 2013 , 114, 244305	2.5	12
293	Fine optical spectroscopy of the 3.45 eV emission line in GaN nanowires. <i>Journal of Applied Physics</i> , 2013 , 113, 043102	2.5	25
292	Structural and optical properties of Al _x Ga _{1-x} N nanowires. <i>Physica Status Solidi - Rapid Research Letters</i> , 2013 , 7, 868-873	2.5	32
291	A RHEED investigation of self-assembled GaN nanowire nucleation dynamics on bare Si and on Si covered with a thin AlN buffer layer. <i>Physica Status Solidi - Rapid Research Letters</i> , 2013 , 7, 835-839	2.5	11
290	Growth, structural and optical properties of GaN/AlN and GaN/GaInN nanowire heterostructures. <i>Physics Procedia</i> , 2012 , 28, 5-16		3
289	Stress-driven island growth on top of nanowires. <i>Physical Review B</i> , 2012 , 86,	3.3	20
288	Growth mechanism and properties of InGaIn insertions in GaN nanowires. <i>Nanotechnology</i> , 2012 , 23, 135703	3.4	63
287	Surface optical phonon modes in GaN nanowire arrays: Dependence on nanowire density and diameter. <i>Physical Review B</i> , 2012 , 85,	3.3	33
286	In situ study of self-assembled GaN nanowires nucleation on Si(111) by plasma-assisted molecular beam epitaxy. <i>Applied Physics Letters</i> , 2012 , 100, 212107	3.4	44
285	Anticrossing of axial and planar surface-related phonon modes in Raman spectra of self-assembled GaN nanowires. <i>Physical Review B</i> , 2012 , 85,	3.3	18
284	Strain state of GaN nanodisks in AlN nanowires studied by medium energy ion spectroscopy. <i>Nanotechnology</i> , 2012 , 23, 425703	3.4	7
283	Temperature-insensitive optical alignment of the exciton in nanowire-embedded GaN quantum dots. <i>Physical Review B</i> , 2011 , 84,	3.3	1
282	Optical anisotropy and light extraction efficiency of MBE grown GaN nanowires epilayers. <i>Optics Express</i> , 2011 , 19, 527-39	3.3	32
281	Nucleation of GaN nanowires grown by plasma-assisted molecular beam epitaxy: The effect of temperature. <i>Journal of Crystal Growth</i> , 2011 , 334, 177-180	1.6	45

280	Polarity of GaN nanowires grown by plasma-assisted molecular beam epitaxy on Si(111). <i>Physical Review B</i> , 2011 , 84,	3.3	89
279	Measuring two dimensional strain state of AlN quantum dots in GaN nanowires by nanobeam electron diffraction. <i>Journal of Physics: Conference Series</i> , 2011 , 326, 012047	0.3	3
278	Counting Tm dopant atoms around GaN dots using high-angle annular dark field images. <i>Journal of Physics: Conference Series</i> , 2011 , 326, 012032	0.3	
277	Effect of Eu-implantation and annealing on the GaN quantum dots excitonic recombination. <i>Nanoscale Research Letters</i> , 2011 , 6, 378	5	6
276	Optical properties of nitride nanostructures. <i>Annalen Der Physik</i> , 2011 , 523, 51-61	2.6	5
275	The role of the annealing temperature on the optical and structural properties of Eu doped GaN/AlN QD. <i>Optical Materials</i> , 2011 , 33, 1045-1049	3.3	3
274	Submicrometre resolved optical characterization of green nanowire-based light emitting diodes. <i>Nanotechnology</i> , 2011 , 22, 345705	3.4	58
273	Structural and optical properties of InGaN/GaN nanowire heterostructures grown by PA-MBE. <i>Nanotechnology</i> , 2011 , 22, 075601	3.4	92
272	Ternary AlGaIn Alloys with High Al Content and Enhanced Compositional Homogeneity Grown by Plasma-Assisted Molecular Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , 2011 , 50, 031001	1.4	5
271	Ternary AlGaIn Alloys with High Al Content and Enhanced Compositional Homogeneity Grown by Plasma-Assisted Molecular Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , 2011 , 50, 031001	1.4	5
270	Functionalizing self-assembled GaN quantum dot superlattices by Eu-implantation. <i>Journal of Applied Physics</i> , 2010 , 108, 084306	2.5	14
269	Optical spectroscopy of cubic GaN in nanowires. <i>Applied Physics Letters</i> , 2010 , 97, 081910	3.4	17
268	Visualization of Tm dopant atoms diffused out of GaN quantum dots. <i>Applied Physics Letters</i> , 2010 , 96, 251908	3.4	22
267	Reversed polarized emission in highly strained a-plane GaN/AlN multiple quantum wells. <i>Physical Review B</i> , 2010 , 82,	3.3	7
266	Influence of Stacking Sequences and Lattice Parameter Differences on the Microstructure of Nonpolar AlN Films Grown on (11 $\bar{2}$ 0) 6H-SiC by Plasma-Assisted Molecular Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , 2010 , 49, 040201	1.4	4
265	Identification of III-N nanowire growth kinetics via a marker technique. <i>Nanotechnology</i> , 2010 , 21, 295605	3.4	53
264	The structural properties of GaN/AlN core-shell nanocolumn heterostructures. <i>Nanotechnology</i> , 2010 , 21, 415702	3.4	67
263	Molecular beam epitaxy growth and optical properties of AlN nanowires. <i>Applied Physics Letters</i> , 2010 , 96, 061912	3.4	45

262	Structural properties of GaN nanowires and GaN/AlN insertions grown by molecular beam epitaxy. <i>Journal of Physics: Conference Series</i> , 2010 , 209, 012010	0.3	5
261	Elastic strain relaxation in GaN/AlN nanowire superlattice. <i>Physical Review B</i> , 2010 , 81,	3.3	41
260	GaN-based nanowires: From nanometric-scale characterization to light emitting diodes. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2010 , 207, 1425-1427	1.6	42
259	Influence of thermal annealing on the structural and optical properties of GaN/AlN quantum dots. <i>Physica Status Solidi (B): Basic Research</i> , 2010 , 247, 1675-1678	1.3	5
258	Growth mechanism of catalyst-free [0001] GaN and AlN nanowires on Si by molecular beam epitaxy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2010 , 7, 2246-2248		6
257	Effect of annealing on AlN/GaN quantum dot heterostructures: advanced ion beam characterization and X-ray study of low-dimensional structures. <i>Surface and Interface Analysis</i> , 2010 , 42, 1552-1555	1.5	4
256	Quantum dot to quantum wire transition of m-plane GaN islands. <i>Physical Review B</i> , 2009 , 79,	3.3	3
255	Optically active centers in Eu implanted, Eu in situ doped GaN, and Eu doped GaN quantum dots. <i>Journal of Applied Physics</i> , 2009 , 105, 043104	2.5	37
254	Structural properties of Ge/Si(001) nano-islands and AlGaIn nanowires by Diffraction Anomalous Fine Structure and Multiwavelength Anomalous Diffraction. <i>Journal of Physics: Conference Series</i> , 2009 , 190, 012129	0.3	6
253	The structural properties of GaN insertions in GaN/AlN nanocolumn heterostructures. <i>Nanotechnology</i> , 2009 , 20, 295706	3.4	20
252	Depth profiling of optical and vibrational properties in GaN/AlN quantum dot superlattices. <i>Physica Status Solidi (B): Basic Research</i> , 2009 , 246, 1191-1195	1.3	3
251	Anisotropic polarization of non-polar GaN quantum dot emission. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009 , 6, S541-S544		2
250	Evidence for quantum-confined Stark effect in GaN/AlN quantum dots in nanowires. <i>Physical Review B</i> , 2009 , 80,	3.3	87
249	Nucleation mechanism of GaN nanowires grown on (111) Si by molecular beam epitaxy. <i>Nanotechnology</i> , 2009 , 20, 415602	3.4	78
248	Polar and nonpolar GaN quantum dots. <i>Journal of Physics Condensed Matter</i> , 2008 , 20, 473201	1.8	24
247	Anisotropic strain state of the [11 $\bar{0}$ 0] GaN quantum dots and quantum wires. <i>Journal of Applied Physics</i> , 2008 , 104, 063521	2.5	3
246	Optical properties of m-plane GaN quantum dots and quantum wires. <i>Journal of Applied Physics</i> , 2008 , 104, 103528	2.5	14
245	Plasma-assisted molecular beam epitaxy growth of GaN nanowires using indium-enhanced diffusion. <i>Applied Physics Letters</i> , 2008 , 93, 183109	3.4	53

244	Measuring local lattice polarity in AlN and GaN by high resolution Z-contrast imaging: The case of (0001) and (11 $\bar{0}$ 0) GaN quantum dots. <i>Applied Physics Letters</i> , 2008 , 92, 201904	3.4	17
243	Exciton and biexciton luminescence from single GaN/AlN quantum dots in nanowires. <i>Nano Letters</i> , 2008 , 8, 2092-6	11.5	86
242	Elastic Strain Distribution in GaN/AlN Quantum Dot Structures: Theory and Experiment. <i>Springer Proceedings in Physics</i> , 2008 , 13-16	0.2	
241	Lattice polarity and capping of GaN dots studied by Z-contrast imaging 2008 , 85-86		
240	Growth and Characterization of Structural and Optical Properties of Polar and Non-polar GaN Quantum Dots 2008 , 201-229		
239	From nucleation to growth of catalyst-free GaN nanowires on thin AlN buffer layer. <i>Applied Physics Letters</i> , 2007 , 91, 251902	3.4	185
238	Vibrational modes and strain in GaN/AlN quantum dot stacks: dependence on spacer thickness. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2007 , 4, 2342-2345		2
237	Evaluation of strain in GaN/AlN quantum dots by means of resonant Raman scattering: the effect of capping. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2007 , 4, 2379-2382		2
236	The growth and rare-earth doping of GaN quantum dots on Al _x Ga _{1-x} N layer by plasma-assisted molecular beam epitaxy. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2007 , 204, 290-293	1.6	2
235	Intentional and unintentional localization in InGaN. <i>Philosophical Magazine</i> , 2007 , 87, 1967-1969	1.6	11
234	GaN quantum dots grown on Al _x Ga _{1-x} N layer by plasma-assisted molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2007 , 102, 024311	2.5	5
233	Anisotropic strain relaxation in a-plane GaN quantum dots. <i>Journal of Applied Physics</i> , 2007 , 101, 063541	2.5	21
232	Raman scattering as a tool for the evaluation of strain in GaN/AlN quantum dots: The effect of capping. <i>Physical Review B</i> , 2007 , 76,	3.3	10
231	Growth of m-plane GaN quantum wires and quantum dots on m-plane 6H-SiC. <i>Journal of Applied Physics</i> , 2007 , 102, 074913	2.5	18
230	Anisotropic morphology of nonpolar a-plane GaN quantum dots and quantum wells. <i>Journal of Applied Physics</i> , 2007 , 102, 074304	2.5	35
229	Grazing-incidence diffraction anomalous fine structure: Application to the structural investigation of group-III nitride quantum dots. <i>Physical Review B</i> , 2007 , 75,	3.3	24
228	Probing exciton localization in nonpolar GaN/AlN quantum dots by single-dot optical spectroscopy. <i>Physical Review B</i> , 2007 , 75,	3.3	56
227	Comparison of the structural quality in Ga-face and N-face polarity GaN/AlN multiple-quantum-well structures. <i>Semiconductor Science and Technology</i> , 2006 , 21, 612-618	1.8	31

226	Optical study of excitation and deexcitation of Tm in GaN quantum dots. <i>Physical Review B</i> , 2006 , 74,	3-3	8
225	Strong electric field and nonuniformity effects in GaN/AlN quantum dots revealed by high pressure studies. <i>Applied Physics Letters</i> , 2006 , 89, 051902	3-4	6
224	Comparison of carrier dynamics in GaN quantum dots and GaN quantum wells embedded in low-Al-content AlGaIn waveguides. <i>Applied Physics Letters</i> , 2006 , 89, 251914	3-4	9
223	GaN quantum dots doped with Tb. <i>Applied Physics Letters</i> , 2006 , 88, 053102	3-4	18
222	Raman study and theoretical calculations of strain in GaN quantum dot multilayers. <i>Physical Review B</i> , 2006 , 73,	3-3	14
221	Resonant Raman scattering in self-assembled GaN/AlN quantum dots. <i>Physical Review B</i> , 2006 , 74,	3-3	20
220	Mechanism of GaN quantum dots capped with AlN: An AFM, electron microscopy, and x-ray anomalous diffraction study. <i>Physical Review B</i> , 2006 , 74,	3-3	23
219	Optical transitions in Eu ³⁺ ions in GaN:Eu grown by molecular beam epitaxy. <i>Physical Review B</i> , 2006 , 73,	3-3	33
218	Step-by-step capping and strain state of GaN/AlN quantum dots studied by grazing-incidence diffraction anomalous fine structure. <i>Physical Review B</i> , 2006 , 73,	3-3	21
217	In situ resonant x-ray study of vertical correlation and capping effects during GaN/AlN quantum dot growth. <i>Applied Physics Letters</i> , 2006 , 88, 153125	3-4	30
216	Eu ³⁺ location in Eu doped GaN thin films and quantum dots. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006 , 3, 2026-2029		
215	Polishing and characterization of thick AlN layers grown on SiC substrates by stress control hydride vapor phase epitaxy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006 , 3, 1448-1452		5
214	Tb-doped GaN quantum dots grown by plasma-assisted molecular beam epitaxy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006 , 3, 2034-2037		1
213	AlN/GaN superlattices: strain relaxation. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006 , 3, 1691-1694		0
212	Quantitative strain analysis of GaN/AlN quantum dot multilayers. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006 , 3, 1667-1670		3
211	Influence of stacking on optical characteristics of GaN/AlN self-organized quantum dots. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006 , 3, 2056-2059		2
210	Influence of strain in the reduction of the internal electric field in GaN/AlN quantum dots grown on a-plane 6H-SiC. <i>Physica Status Solidi (B): Basic Research</i> , 2006 , 243, 1499-1507	1-3	9
209	Undoped and rare-earth doped GaN quantum dots on AlGaIn. <i>Physica Status Solidi (B): Basic Research</i> , 2006 , 243, 1472-1475	1-3	4

208	In situ and ex situ grazing incidence diffraction anomalous fine structure study of GaN/AlN quantum dots. <i>Physica Status Solidi (B): Basic Research</i> , 2006 , 243, 1519-1523	1.3	3
207	Optical properties of single non-polar GaN quantum dots. <i>Physica Status Solidi (B): Basic Research</i> , 2006 , 243, 1652-1656	1.3	10
206	Growth of GaN quantum dots on nonpolar A -plane SiC by molecular-beam epitaxy. <i>Physica Status Solidi (B): Basic Research</i> , 2006 , 243, 3968-3971	1.3	12
205	Comparative optical study of Eu ³⁺ ions doping in InGaN/GaN quantum dots and GaN layer grown by molecular beam epitaxy. <i>Optical Materials</i> , 2006 , 28, 775-779	3.3	6
204	Grazing incidence diffraction anomalous fine structure study of GaN/AlN quantum dots. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2006 , 246, 58-63	1.2	5
203	Strain distribution in GaN/AlN quantum-dot superlattices. <i>Applied Physics Letters</i> , 2005 , 87, 203112	3.4	67
202	Eu locations in Eu-doped InGaN/GaN quantum dots. <i>Applied Physics Letters</i> , 2005 , 87, 021906	3.4	18
201	Study of isolated cubic GaN quantum dots by low-temperature cathodoluminescence. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2005 , 26, 203-206	3	37
200	Raman study of strain in GaN/AlN quantum dot multilayered structures. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005 , 2, 2328-2331		3
199	GaN quantum dots grown on non-polar a-plane SiC by plasma-assisted molecular beam epitaxy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005 , 2, 2341-2344		1
198	Rare-earth doped GaN and InGaN quantum dots grown by plasma assisted MBE. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005 , 2, 2373-2376		6
197	Phase transition by Mg doping of N-face polarity GaN. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005 , 2, 2216-2219		2
196	Reduction of the internal electric field in GaN/AlN quantum dots grown on the a -plane of SiC substrates. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005 , 2, 3851-3855		
195	Optical properties of GaN quantum dots grown on nonpolar (11-20) SiC by molecular-beam epitaxy. <i>Applied Physics Letters</i> , 2005 , 86, 171901	3.4	59
194	Deformation profile in GaN quantum dots: Medium-energy ion scattering experiments and theoretical calculations. <i>Physical Review B</i> , 2005 , 72,	3.3	24
193	Reduction of the internal electric field in wurtzite a-plane GaN self-assembled quantum dots. <i>Applied Physics Letters</i> , 2005 , 87, 011101	3.4	32
192	Optical and morphological properties of GaN quantum dots doped with Tm. <i>Physical Review B</i> , 2005 , 71,	3.3	23
191	GaN quantum dots: from basic understanding to unique applications. <i>Journal of Physics: Conference Series</i> , 2005 , 10, 61-68	0.3	6

190 Structural properties of GaN quantum dots **2005**, 3-12

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23	Proton channeling anomalies in the blue bronze K _{0.30} MoO ₃ . <i>Synthetic Metals</i> , 1989 , 29, 227-234	3.6	9
22	Axial channeling by an intersecting plane potential. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1988 , 34, 439-443	1.2	
21	Modification of the ferroelectric properties of vinylidene fluoride trifluoro-ethylene copolymers induced by electron irradiation. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1988 , 32, 177-181	1.2	20
20	MeV ion beam enhanced adhesion of Au films on alumina. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1988 , 34, 181-187	1.2	7
19	Electron irradiation effects in ferroelectric vinylidene fluoride trifluoro-ethylene copolymers. <i>Ferroelectrics</i> , 1988 , 81, 357-360	0.6	11
18	Effects of electron irradiation and annealing on ferroelectric vinylidene fluoride-trifluoroethylene copolymers. <i>Journal of Applied Physics</i> , 1987 , 62, 994-997	2.5	67
17	CDW transport in the blue bronze and related phenomena. <i>Synthetic Metals</i> , 1987 , 19, 917-922	3.6	2
16	Properties of amorphous carbon films deposited by ion beam methods. <i>Thin Solid Films</i> , 1987 , 148, 311-321	2.2	16
15	Some investigations of MeV ion-beam enhanced adhesion. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1987 , 19-20, 114-119	1.2	6
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13	Lattice dynamics of LaB ₆ studied by ion channeling: La in the Einstein model. <i>Physical Review B</i> , 1986 , 34, 8367-8371	3.3	11
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11	Ion dechanneling in layered dichalcogenides 1T-TaS ₂ and 1T-TiSe ₂ . <i>Solid State Communications</i> , 1985 , 54, 457-460	1.6	6

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